

AMENDED CLAIM SET

1. (Currently Amended) A charge pump circuit for supplying a boosted voltage to a memory device, comprising:

a charge pump part constructed with first to nth unit charge pumps; and

a multi-level detector that detects a level variation of the boosted voltage and outputs first to nth level detection signals for selectively driving corresponding individual unit charge pumps, the multi-level detector including:

a voltage distributor for dividing the boosted voltage into first to nth voltage levels; and

first to nth level detectors for comparing the first to nth voltage levels with a reference level and generating the first to nth level detection signals[[]];

an oscillator for producing a pulse signal in accordance with the first level detection signal from the first level detector; and

a logic operation part for logically operating the pulse signal of the oscillator and the second to nth level detection signal from the second to nth level detectors, and outputting first to nth operated signals to the first to nth unit charge pumps.

2. (Cancelled).

3. (Original) The charge pump device of claim 1, wherein the first unit charge pump is always driven by the level detection signal output from the multi-level detector.

4. (Cancelled).

5. (Previously Presented) The charge pump device of claim 1, wherein the second to nth unit charge pumps are selectively driven in accordance with the level of the boosted voltage.

6. (Cancelled).

7. (Original) The charge pump device of claim 1, wherein each of the first to nth level detectors includes a differential amplifier.

8. (Previously Presented) The charge pump device of claim 1, wherein the first voltage level is lower than the reference level.

9. (Currently Amended) A charge pump device associated with a memory device, comprising:

a charge pump part including first to nth unit charge pumps to generate a boosted voltage;

a multi-level detector that detects a level of the boosted voltage and outputs first to nth level detection signals for selectively driving corresponding individual unit charge pumps,

wherein the first unit charge pump is always driven by the first level detection signal output from the multi-level detector, and each of the first to nth level detectors is composed of a different amplifier[[]]; and

wherein the second to nth unit charge pumps are selectively driven in accordance with the level of the boosted voltage.

10. (Previously Presented) The charge pump device of claim 9, wherein the multi-level detector includes:

a voltage distributor for dividing the boosted voltage into first to nth voltage levels; and

first to nth level detectors for detecting a plurality of levels of the boosted voltage by comparing the first to nth voltage levels divided by the voltage distributor with a reference level.

11. (Cancelled).

12. (Previously Presented) The charge pump device of claim 10, wherein the first voltage level is lower than the reference level.

13. to 17. (Cancelled).